Claims 1-20 were pending prior to the instant amendment. By this amendment, claims 1, 2, 4-6, 8-10, 12-14, 16, 17 and 19 are amended, and new claims 21-26 are added to recite additional features of the present invention to which Applicants are entitled that were previously recited in the pending independent claims 1, 5, 9, 13, 17, and 19. Consequently, claims 1-26 are currently pending in the instant application.

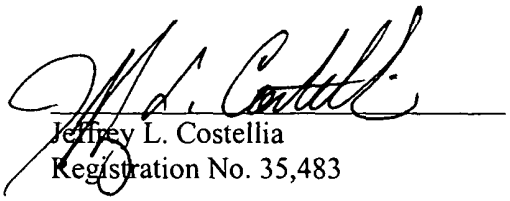
With respect to the Office Action, claims 1-16 are rejected under 35 U.S.C. §103(a) over Mei et al., in view of Soh; and claims 17-20 are rejected under 35 U.S.C. §103(a) over Mei et al., in view of Soh, further in view of Czubatyj et al. These rejections are traversed for the reasons advanced below.

The effective date as a reference of the Mei et al. reference is June 7, 1993, and the effective date of Soh et al. as a reference is December 30, 1992. On the other hand, the priority date of the instant application is at least August 27, 1992. As a result, Applicant intends to file a verified translation of the priority application (Japanese application No. 4-252295) to remove these patents as references against the claims of the instant application.

In addition, independent claims 1, 5, 9, 13, 17 and 19 are amended to remove the limitation of "excimer" laser from the claims. New claims 21-26 are added to recite this feature of the present invention to which Applicants are entitled. Consideration and allowance of these claims are respectfully requested.

In view of the foregoing, it is respectfully requested that the rejections of record be reconsidered and withdrawn by the Examiner, that claims 1-20 be allowed, that new claims 21-26 be allowed and that the application be passed to issue. If a conference would expedite prosecution of the instant application, the Examiner is hereby invited to telephone the undersigned to arrange such a conference.

Respectfully submitted,



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ATTACHMENT TO AMENDMENT

1. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands over a glass substrate;

subjecting said semiconductor islands to an ion doping;

directing a pulsed [excimer] laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed [excimer] laser beam, thereby irradiating said semiconductor islands with said pulsed [excimer] laser beam.

2. (Amended) A method according to claim 1 wherein an energy density of said pulsed [excimer] laser beam is not higher than 300 mJ/cm^2.

4. (Amended) A method according to claim 1 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed [excimer] laser beam.

5. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a glass substrate;

crystallizing said semiconductor film;

patterning the crystallized semiconductor film into a plurality of semiconductor islands;

subjecting said semiconductor islands to an ion doping;

directing a pulsed [excimer] laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to :the elongation direction of said pulsed [excimer] laser beam, thereby irradiating said semiconductor islands with said pulsed [excimer] laser beam.

6. (Amended) A method according to claim *5* wherein an energy density of said pulsed [excimer] laser beam is not higher than 300 mJ/cm^2.

8. (Amended) A method according to claim *5* wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed [excimer] laser beam.

9. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of first semiconductor islands and a plurality of second semiconductor islands over a glass substrate;

subjecting both of said first and second semiconductor islands to a first ion doping for introducing a first impurity;

subjecting only said first semiconductor islands to a second ion doping for introducing a second impurity wherein said second impurity has an opposite conductivity type to said first impurity;

directing a pulsed [excimer] laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed [excimer] laser beam, thereby irradiating both of said first and second semiconductor islands with said pulsed [excimer] laser beam.

10. (Amended) A method according to claim 9 wherein an energy density of said pulsed [excimer] laser beam is not higher than 300 mJ/cm^2.

12. (Amended) A method according to claim 9 wherein each of said first and second semiconductor islands is irradiated with plural pulses of said pulsed [excimer] laser beam.

13. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands over a glass substrate;

forming a film comprising silicon oxide over said glass substrate wherein said

semiconductor islands are covered by said film;

subjecting said semiconductor islands to an ion doping through said film;

directing a pulsed [excimer] laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed [excimer] laser beam, thereby irradiating said semiconductor islands with said pulsed [excimer] laser beam through said film.

14. (Amended) A method according to claim 13 wherein an energy density of said pulsed [excimer] laser beam is not higher than 300 mJ/cm^2.

16. (Amended) A method according to claim 13 wherein each of said semiconductor islands is irradiated with plural pulses of said pulsed [excimer] laser beam.

17. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands comprising silicon and germanium over a substrate;

subjecting said semiconductor islands to an ion doping;

directing a pulsed [excimer] laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed [excimer] laser beam, thereby irradiating said semiconductor islands with said pulsed [excimer] laser beam.

19. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

preparing a plurality of semiconductor islands comprising silicon and germanium over a substrate;

forming a film comprising silicon oxide over said glass substrate wherein said semiconductor islands are covered by said film;

subjecting said semiconductor islands to an ion doping through said film;

directing a pulsed [excimer] laser beam having a cross section elongated in one direction to said glass substrate;

moving said glass substrate in a direction perpendicular to the elongation direction of said pulsed [excimer] laser beam, thereby irradiating said semiconductor islands with said pulsed [excimer] laser beam through said film.